

AMENDMENTS TO THE CLAIMS:

Please amend the claims as indicated below:

11. **(Withdrawn)** A method for etching a substrate, comprising:

placing a substrate in an etching chamber;

introducing at least one of a first etchant and a first etch catalyst originating from a first source into said etching chamber via an auxiliary chamber positioned within a first path, said introducing comprising intermittently closing an inlet of the auxiliary chamber after introduction of said at least one of a first etchant and a first etch catalyst followed by opening an outlet of the auxiliary chamber to discharge said at least one of a first etchant and first etch catalyst into said etching chamber, such that the inlet is closed when the outlet is opened;

introducing at least one of a second etchant and a second etch catalyst originating from a second source via a second path;

etching said substrate;

flushing said etching chamber; and

removing said substrate from said etching chamber.

12. **(Withdrawn)** The method of Claim 11, wherein said flushing of said etching chamber is carried out via said auxiliary chamber, said auxiliary chamber being evacuated after etching and prior to refilling the auxiliary chamber.

13. **(Withdrawn)** The method of Claim 11, further comprising shutting off said at least one of a second etchant and a second etch catalyst to said chamber when said auxiliary chamber is connected to said etching chamber.

14. **(Withdrawn)** The method of Claim 11, wherein the first etchant is hydrogen fluoride.

15. **(Currently Amended)** An installation for etching a substrate, comprising:

and a second fluid feed, wherein the first fluid feed is connected at a source end to a

source of a first etching gas, wherein the ~~and~~ second fluid feeds is connected at a source
end to a source of a second etching gas, and wherein the first and second fluid feeds are
configured to separately provide the first and second etching ~~fluids~~ gases to the etching
chamber via the piping system; and

an auxiliary chamber positioned within the piping system and having an inlet and
an outlet, wherein the inlet includes a controllable shut-off valve and is in communication
with the first fluid feed, wherein the outlet includes a controllable shut-off valve and is in
communication with the etching chamber, and wherein only one of said shut-off valves is
open at a time.

16. **(Previously Added)** The installation of Claim 15, wherein the piping system
includes a bypass line for bypassing said auxiliary chamber.

17. **(Previously Added)** The installation of Claim 15, wherein said etching chamber
is connected to a vacuum pump.

18. **(Previously Added)** The installation of Claim 15, wherein the piping system
includes a valve coupled to the second fluid feed.

19. **(Previously Added)** The installation of Claim 15, wherein said etching chamber
is of a plastic material and is configured to withstand a reduced pressure in said etching chamber.

20. **(Previously Added)** The installation of Claim 19, wherein said plastic material
comprises polyvinylidene fluoride.

21. **(New)** The installation of Claim 15, wherein the first etching gas comprises
hydrogen fluoride.

22. **(New)** The installation of Claim 21, wherein the second etching gas is a catalyst
for hydrogen fluoride etching.

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24. (New) The installation of Claim 23, wherein the second etching gas comprises acetic acid.